

Docket: TSMC 00 - 299C
S/N: TBD

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

From: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Continuation Application Based upon Application
Serial No.: 09/932,730, Filed: 08/20/01

Inventor: Chao-Chieh Tsai

Title: High f_{MAX} Deep Submicron MOSFET

Group Art Unit: TBD Examiner: TBD
Attorney Docket: TSMC 00 - 299C


PRELIMINARY AMENDMENT

Dear Sir:

As a Preliminary Amendment for the above-identified
Continuation Application filed concurrently herewith, please consider the
following remarks.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with
the United States Postal Service as first class mail in an envelope addressed to:
Commissioner of Patent and Trademarks, Washington, D.C. 20231, on
July 21, 2003.

Signature/Date  July 21, 2003

Stephen B. Ackerman
Reg. No. 37,761

July 18, 2003

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Continuation of
Serial No.: 09/932,730 8/20/01

CHAO-CHIEH TSAI, SHYH-CHYI WONG,
CHUNG-LONG CHANG

HIGH F_{MAX} DEEP SUBMICRON MOSFET

PRELIMINARY AMENDMENT

Dear Sir:


This is a preliminary amendment for the above referenced Continuation. Please amend the above identified application for patent as follows:

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks, Washington, D.C. 20231, on July 21, 2003.

Stephen B. Ackerman, Reg. No. 37,761

Signature/Date

 7/21/03